imall

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30V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

 $V_{(BR)DSS}$ =30V; $R_{DS(ON)}$ =0.025 Ω I_D=6.7A

DESCRIPTION

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- · Fast switching speed
- Low threshold
- Low gate drive
- Low profile SOIC package

APPLICATIONS

- DC DC Converters
- Power Management Functions
- Disconnect switches
- Motor control

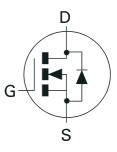
ORDERING INFORMATION

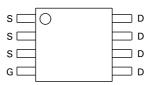
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMN3A02X8TA	7″	12mm	1000 units
ZXMN3A02X8TC	13″	12mm	4000 units

DEVICE MARKING

 ZXMN 3A02







Top View



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DSS}	30	V
Gate Source Voltage	VGS	±20	V
Continuous Drain Current $V_{GS}=10V$; $T_A=25^{\circ}C$ (b) $V_{GS}=10V$; $T_A=70^{\circ}C$ (b) $V_{GS}=10V$; $T_A=25^{\circ}C$ (a)	ID	6.7 5.4 5.3	A
Pulsed Drain Current (c)	IDM	24	А
Continuous Source Current (Body Diode) (b)	IS	3.2	А
Pulsed Source Current (Body Diode) (c)	ISM	24	А
Power Dissipation at T _A =25°C (a) Linear Derating Factor	PD	1.1 8.8	W mW/°C
Power Dissipation at T _A =25°C (b) Linear Derating Factor	PD	1.8 14.4	W mW/°C
Operating and Storage Temperature Range	Tj:Tstg	-55 to +150	°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	R ₀ JA	113	°C/W
Junction to Ambient (b)	R _{0JA}	70	°C/W

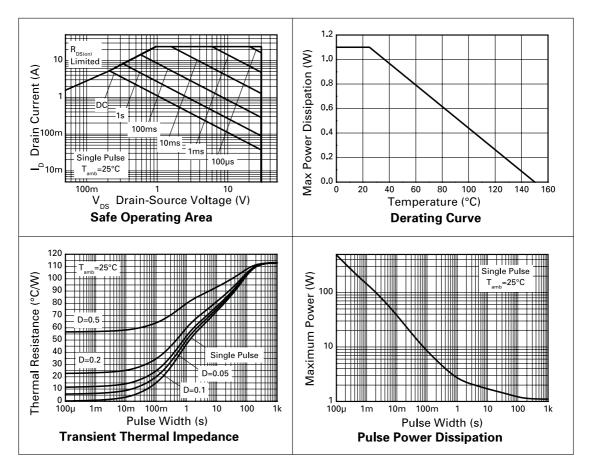
NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

(b) For a device surface mounted on FR4 PCB measured at t ${\leqslant}10$ secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width $10\mu s$ - pulse width limited by maximum junction temperature.





CHARACTERISTICS

* For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.



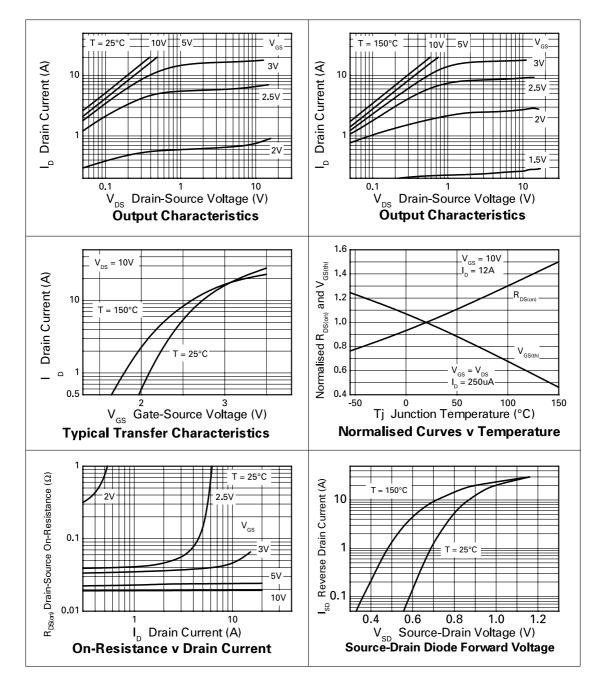
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.	
STATIC		1	1		1		
Drain-Source Breakdown Voltage	V(BR)DSS	30			V	I _D =250μA, V _{GS} =0V	
Zero Gate Voltage Drain Current	IDSS			1	μA	V _{DS} =30V, V _{GS} =0V	
Gate-Body Leakage	IGSS			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Gate-Source Threshold Voltage	VGS(th)	1			V	I _D =250μA, V _{DS} = V _{GS}	
Static Drain-Source On-State Resistance (1)	R _{DS(on)}			0.025 0.035	Ω Ω	V _{GS} =10V, I _D =12A V _{GS} =4.5V, I _D =10.2A	
Forward Transconductance (1)(3)	9fs		22		S	V _{DS} =10V,I _D =12A	
DYNAMIC (3)							
Input Capacitance	C _{iss}		1400		pF		
Output Capacitance	C _{oss}		209		pF	V _{DS} =25 V, V _{GS} =0V, f=1MHz	
Reverse Transfer Capacitance	C _{rss}		120		pF	1	
SWITCHING(2) (3)							
Turn-On Delay Time	^t d(on)		3.9		ns		
Rise Time	t _r		5.5		ns	$V_{DD} = 15V, I_{D} = 5.5A$	
Turn-Off Delay Time	^t d(off)		35.0		ns	R_{G} =6.2 Ω , V_{G} S=10V (refer to test circuit)	
Fall Time	t _f		7.6		ns		
Gate Charge	٥ _g		14.5		nC	V _{DS} =15V,V _{GS} =5V, I _{D=5.5A} (refer to test circuit)	
Total Gate Charge	٥ _g		26.8		nC	-VDS=15V,VGS=10V, ID=5.5A (refer to test circuit)	
Gate-Source Charge	0 _{gs}		4.7		nC		
Gate-Drain Charge	Qgd		4.7		nC		
SOURCE-DRAIN DIODE							
Diode Forward Voltage (1)	V _{SD}			0.95	V	TJ=25°C, IS=9A, VGS=0V	
Reverse Recovery Time (3)	t _{rr}		17		ns	TJ=25°C, IF=5.5A, di/dt= 100A/μs	
Reverse Recovery Charge (3)	0 _{rr}		8.3		nC		

NOTES

(1) Measured under pulsed conditions. Width=300 $\mu s.$ Duty cycle $\leq 2\%$. (2) Switching characteristics are independent of operating junction temperature.

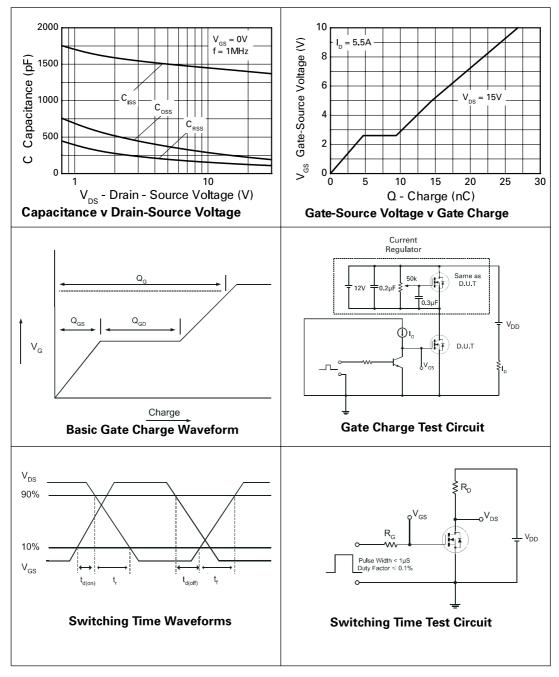
(3) For design aid only, not subject to production testing.





CHARACTERISTICS





CHARACTERISTICS



Inches

MAX

0.043

0.006

0.016

0.009

0.122

BSC

0.122

BSC

0.028

6°

MIN

0.002

0.010

0.005

0.114

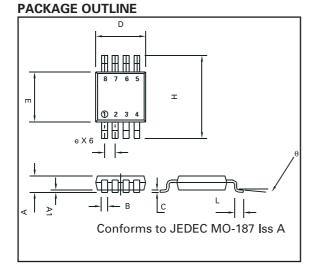
0.0256

0.114

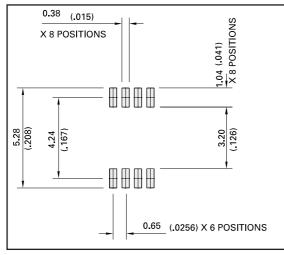
0.193

0.016

0°



PAD LAYOUT



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PACKAGE	DIMENSION
FACKAGE	DIMENSION

MIN

0.05

0.25

0.13

2.90

0.65

2.90

4.90

0.40

0°

Millimetres

MAX

1.10

0.15

0.40

0.23

3.10

BSC

3.10

BSC

0.70

6°

DIM

А

A1

В

С

D

е

Е

Н

L

 θ°